

Docket No: H1598**Serial No. 10/772,830****SPECIFICATION**

Please amend the specification as follows:

Page 5, please amend the paragraphs from line 1 to line 10 as follows:

As is shown in Figure 2B, the patterned layer of photoresist 206a has a ~~patterned~~ pattern formed therein according to processes known to those of skill in the art. In one instance the pattern formed could be for trenches, although any pattern suitable for semiconductor fabrication could be utilized. Thus, the present invention is not applicable to only trench formation. Rather, the present invention can be utilized in a wide variety of situations where sub-lithographic dimensions are desired.

The trenches ~~212~~ 208 can be formed to have any desired width (e.g., a width in the range of about 0.05 microns to about 5 microns). As is shown in Figure 2B, trenches ~~212~~ 208 have a width A which typically will be towards the upper resolution limit of the photoresist patterning process.

Page 6, please amend the paragraph from lines 26-31 as follows:

As is shown in Figure 2C, the conforming layer 210 is deposited both on the horizontal and vertical surfaces of the patterned photoresist ~~208a~~ 206a. It should be noted that the present invention is not limited to embodiments where only horizontal and vertical surfaces are present. Instead the present invention can be utilized to deposit a conforming layer over a wide variety of patterns, be the patterns trench patterns or other types of semiconductor patterns.

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Page 7, please amend the paragraph at lines 29-31 as follows:

Next in Step S108 conforming film 210 is ~~etch~~ etched anisotropically to yield sidewall spaces spacers 210a as shown in Figure 2E. Anisotropic etching processes are known to those of skill in the art, and as such a discussion hereof is omitted for brevity.